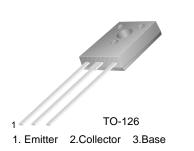
January 2011



KSC5026M NPN Silicon Transistor

Features

- High Voltage and High Reliability
- High Speed Switching
- Wide SOA



Symbol	Parameter	Value	Units V	
V _{CBO}	Collector-Base Voltage	1100		
V _{CEO}	Collector-Emitter Voltage	800	V	
V _{EBO}	Emitter-Base Voltage	7	V	
I _C Collector Current (DC) I _{CP} Collector Current (Pulse)		1.5	A	
		5	A	
I _B Base Current		0.8	А	
P _C	Collector Dissipation (T _C =25°C)	20	W	
Τ _J	Junction Temperature	150	°C	
T _{STG}	Storage Temperature	- 55 to 150	°C	

Absolute Maximum Ratings $T_A = 25^{\circ}C$ unless otherwise noted

Package Marking and Ordering Information

Part Number	Marking	Package	Packing Method	Remarks
KSC5026MOS*	C5026M-O	TO-126	BULK	

* The suffix "M" & "S" of FSID denotes TO126 package and the suffix "O" of FSID denotes h_{FE}-class

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 1$ mA, $I_{\rm E} = 0$	1100			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 5mA, I _B = 0	800			V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_{E} = 1 \text{mA}, I_{C} = 0$	7			V
V _{CEX} (sus)	Collector-Emitter Sustaining Voltage	I _C = 0.75A, I _{B1} = -I _{B2} = 0.15A, L = 5mH, Clamped	800			V
I _{CBO}	Collector Cut-off Current	$V_{CB} = 800V, I_E = 0$			10	μA
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$			10	μA
h _{FE1} h _{FE2}	DC Current Gain	$V_{CE} = 5V, I_{C} = 0.1A$ $V_{CE} = 5V, I_{C} = 0.5A$	10 8		40	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C = 0.75A, I _B = 0.15A			2	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	I _C = 0.75A, I _B = 0.15A			1.5	V
C _{ob}	Output Capacitance	$V_{CB} = 10V, I_E = 0, f = 1MHz$		35		pF
f _T	Current Gain Bandwidth Product	V _{CE} = 10V, I _C = 0.1A		15		MHz
t _{ON}	Turn On Time	V _{CC} = 400V			0.5	μS
t _{STG}	Storage Time	$I_{C} = 5I_{B1} = -2.5I_{B2} = 1A$			3	μs
t _F	Fall Time	$R_L = 400\Omega$			0.3	μs

Electrical Characteristics $T_A = 25^{\circ}C$ unless otherwise noted

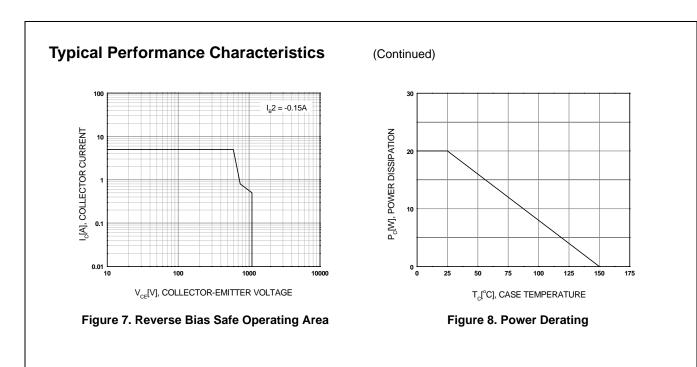
h_{FE} Classification

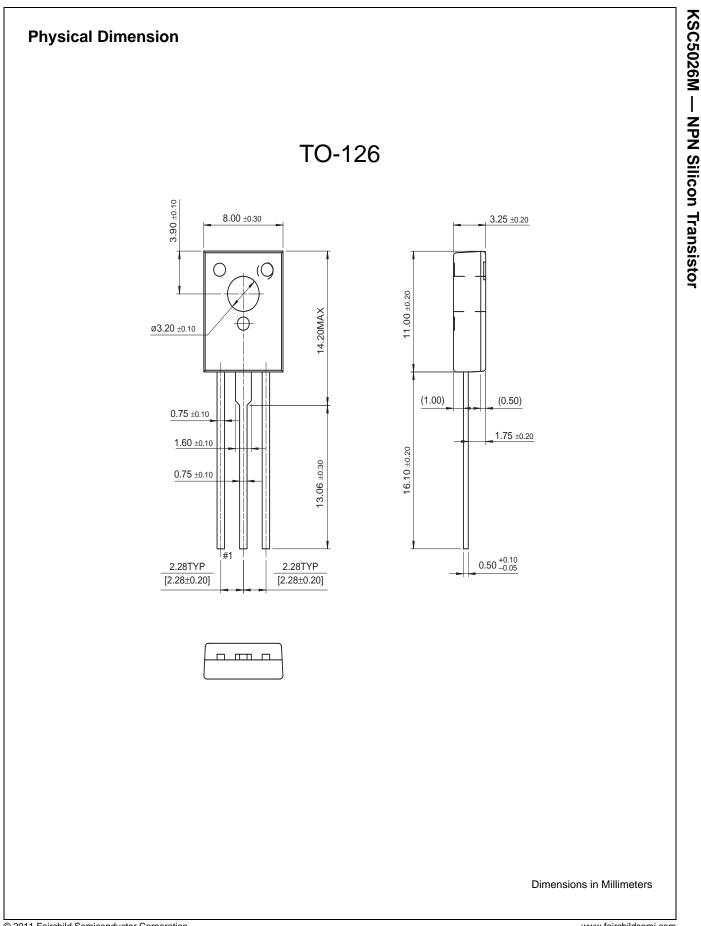
Classification	Ν	R	0
h _{FE1}	10 ~ 20	15 ~ 30	20 ~ 40

Typical Performance Characteristics 2.0 1000 $V_{CE} = 5V$ 1.8 I_c[A], COLLECTOR CURRENT 1.6 h_{FE}, DC CURRENT GAIN 1.4 100 1.2 = 120mA 1.0 = 100mA = 80mA 0.8 = 60 m/s10 = 40mA 0.6 I_B = 20mA 0 I_B = 10mA 0. $I_{B} = 5 mA$ I_B = 0 0.0 1 – 0.01 5 9 10 0.1 10 2 3 6 8 100 I_c[A], COLLECTOR CURRENT V_{CE}[V], COLLECTOR-EMITTER VOLTAGE Figure 1. Static Characteristic Figure 2. DC current Gain 1.6 $V_{\rm BE}({\rm sat}),\,V_{\rm CE}({\rm sat})[V],\,{\rm SATURATION}\,\,{\rm VOLTAGE}$ 10 $V_{CE} = 5V$ I_c = 5 I_B 1.4 I_c[A], COLLECTOR CURRENT 1.2 1 1.0 0.8 0.6 0.1 /__(sat 0.4 0.2 0.01 -0.01 0.0 └-0.0 0.1 1 0.2 0.4 0.6 0.8 1.0 1.2 10 I_c[A], COLLECTOR CURRENT V_{BE}[V], BASE-EMITTER VOLTAGE Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage Figure 4. Base-Emitter On Voltage 10 I_c(max).(Pulse) Ic[A], COLLECTOR CURRENT I_c(max) t_{ov}, t_{s⊤e}, t_F [µs], TIME 0.1 0.1 0.01 0.01 L 0.1 1E-3 ^L 1 1 10 100 10 1000 I_c[A], COLLECTOR CURRENT V_{CE}[V], COLLECTOR-EMITTER VOLTAGE Figure 5. Switching Time Figure 6. Safe Operating Area

KSC5026M — NPN Silicon Transistor

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